MAINTENANCE MANUAL SYNTHESIZER BOARD B19/CMG-185

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DESCRIPTION

SYNTHESIZER

The frequency synthesizer generates the transmitter output frequency and the receiver first mixer injection frequency. The synthesizer board (CMG-1 85) mounts in the top section of the frame assembly as shown in Figure 1.

CIRCUIT ANALYSIS

The frequency synthesizer circuit (Figure 2 and schematic diagram) consists of reference oscillator XU201, synthesizer chip IC201, dual-modulus prescaler IC204, RX and Tx Voltage Controlled Oscillators (VCOs) TR203 and TR209, a loop filter and associated circuitry.

REFERENCE OSCILLATOR

Reference oscillator XU201 operates at a frequency of 13.2 MHz and is temperature compensated to provide a frequency stability of ± 1.5 ppm. Voltage for the oscillator is supplied by 9-volt regulator IC209 and 4-volt Zener diode CD201. The oscillator output is applied to synthesizer chip IC201 -2. Synthesizer IC201 (Figure 3) consists of a Programmable R counter, phase detector, and programmable VCO dividers (N and A).

When the microcontroller desires to change transmit or receive frequencies, new frequency data is received on the CLOCK, DATA, and ENABLE lines. The synthesizer immediately begins generating the new frequency.

The serial data (DATA line) sets the internal VCO dividers which determines the VCO frequency. The reference oscillator frequency applied to the programmable reference oscillator divider (R counter) is divided down to a lower frequency determined by the input data. The lower frequency output is applied to the internal phase detector. The phase detector compares this signal with the output of the internal programmable VCO dividers. The output of the programmable VCO dividers is a function of the rf frequency which is divided down by the dual-modulus prescaler and the programmable VCO dividers.

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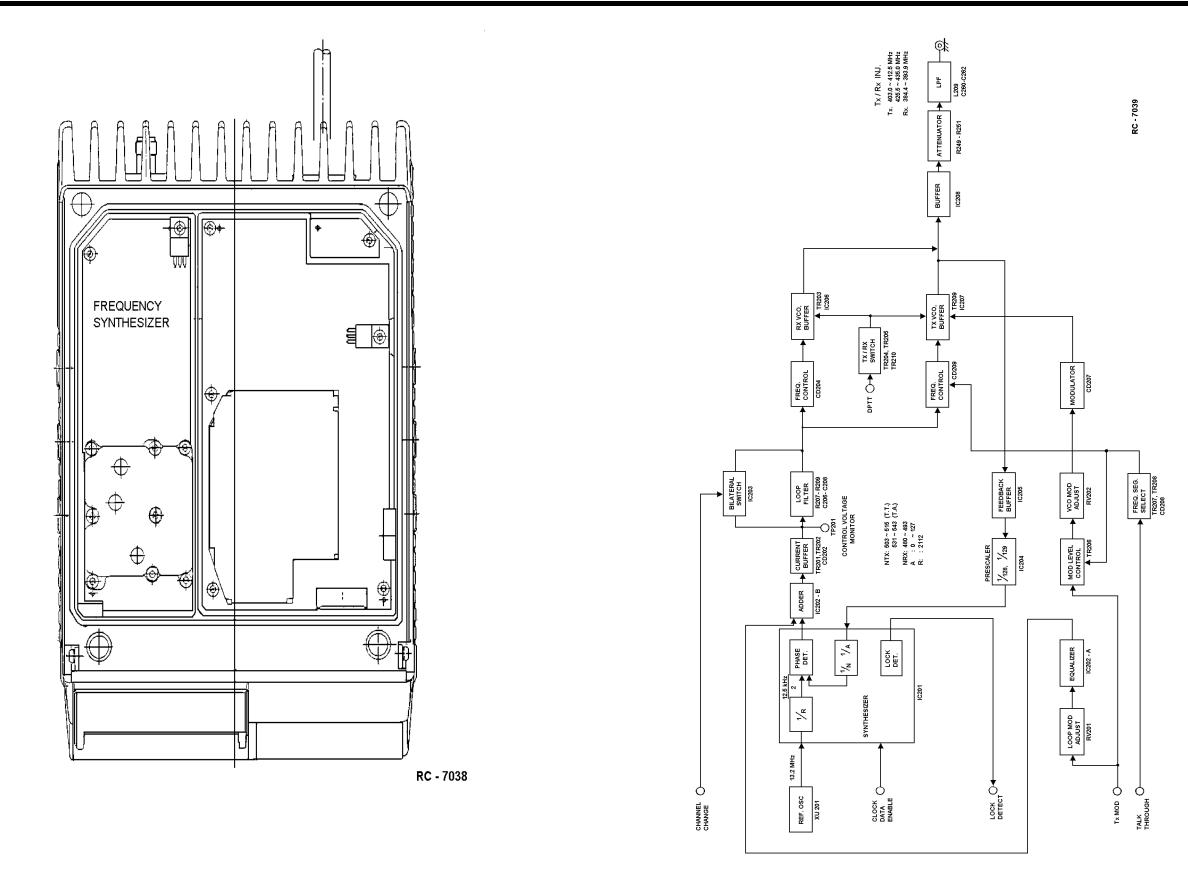


Figure 1 - Synthesizer Location (Top View)

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Figure 2 - Synthesizer Block Diagram

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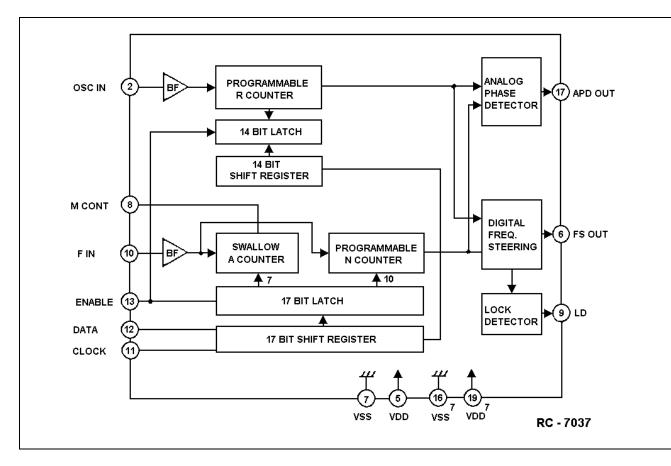


Figure 3 - Synthesizer IC201

When operating on the correct frequency, the inputs to the phase detector are identical and the output voltage of the phase detector is constant. Under these conditions, the VCO is stabilized and locked on frequency. If the compared frequencies (phases) differ, an error voltage is generated and applied to the VCO through the frequency-acquisition circuit, causing the Phase-Lock Loop (PLL) to acquire the new frequency.

The LOCK DETECT (LD) line provides the PLL status information to the microcontroller. When the PLL is out of lock, the LOCK DETECT line is low. When locked on frequency, the line is high.

EQUALIZER

The equalizer (see schematic diagram) consisting of IC202-A, R21 8, R21 9, and C220, receives transmit audio from LOOP MOD adjust RV201 and provides the required audio level. The output of the equalizer (LOOP MOD) is summed with the output signal from the phase detector (BIAS) by adder IC202-B

DC OFFSET AND HIGH-CURRENT BUFFERS

DC offset buffers TR201, TR202, and CD202 (see schematic diagram) receive the error voltage from the equalizer and increase this level by 1.8 Vdc to extend the operating range of the high-current buffers. When the PLL is off frequency due to a channel change or frequency drift, the error voltage from the synthesizer (APD OUT) rises or falls turning TR201 on or off. Transistor TR201 controls the dc offset buffer (TR202 and CD202). Resistors R206, R208, and R209 provide a high-current, rapid-charge path between the + 9 volt supply and C206 and C208. Transistor TR202 and CD202 provide a rapid discharge path for the capacitors.

As the error voltage decreases, transistors TR201 and TR202 turn on completing a discharge path for C206 thru C208 through bilateral switches IC203. When the error voltage goes positive TR201, TR202, and CD202 are turned off, allowing C206 thru C208 to charge through R206. IC203 is turned on for 15 milliseconds when a channel is changed.

LOOP FILTER

The loop filter (see schematic diagram) consists of R207 thru R209 and C206 thru C208. This filter controls the bandwidth and stability of the synthesizer loop.

Bilateral switch IC203 is controlled by the 4 millisecond, 9 volt channel change (CH. CHANGE) pulse. When the channel change pulse is present, the bilateral switch shorts out the low-pass filter, increasing the loop bandwidth to achieve the 4 millisecond channel acquisition time required for dual-priority scan.

The low-pass filter removes noise and other extraneous signals Internal to the synthesizer chip. The output of the filter is applied to the varicaps in the transmit and receive VCOs to adjust or correct the VCO frequency.

RECEIVE VCO

The receiver VCO (see schematic diagram) consists of a low-noise JFET oscillator (TR203) followed by high-gain buffer IC206. This buffer prevents external loading and improves power gain.

The VCO is a Colpitts oscillator with varactor C225 and L203 forming the tank circuit. Variable capacitor CV201 allows manual adjustment of the VCO across the frequency split. The VCO operates over a frequency range of 384.4 to 393.9 MHz.

The VCO switches on and off under control of the DPTT line. When the DPTT line is low, the receiver VCO is turned on (TR204 is off and TR205 is on). Buffer IC206 provides a typical output of +5 dBm.

TRANSMIT VCO

The transmit VCO (TR209) is basically the same as the receiver VCO. The wide band VCO allows frequency separation of 45 MHz as determined by the band-split of the radio (806-825 MHz or 851-870 MHz). The varactor in conjunction with the frequency segment selector circuitry (TR207, TR208, and PIN diode CD208) provides a voltage controlled adjustment range that extends across the entire frequency split.

The VCO operates over frequency ranges of 403-41 2.5 MHz and 425.5-435.0 MHz. Buffer IC207 provides a typical output of + 5 dBm. Transmit audio is applied to modulation adjustment control RV202 (VCO MOD ADJ). Deviation is set for 3.75 kHz (3.0 kHz NPSPAC).

The TX VCO control switch TR210 turns the Transmit VCO on when DPTT is high (TR210 is on). The use of two

VCOs allows rapid independent selection of transmit and receive frequencies across the frequency split.

Frequency Segment Selector

The frequency segment selector switches capacitance in and out of the TX VCO tank circuit to select the frequency segment containing the channel. The frequency segment selector consists of TR207, TR208, and CD208 and operates under control of the microcontroller through transistor TR706. Capacitor C243 is selected or deselected for operation in a given segment. Table 1 identifies the circuit conditions and capacitor used for selection of each segment.

Та

SEGMENT	FREQUENCY SPLIT (MHZ)			PIN DIODE CD208	GROUNDED CAPACITOR	GROUNDED RESISTOR
1	Tx: 806-825 RX: 851-870	ON	OFF	ON	C243	NONE
2	Tx: 851-870 RX: 851-870	OFF	ON	OFF	NONE	R232

Reverse bias to turn PIN diode CD208 off is provided by the + 8 volt filtered supply through resistor R240. Forward bias for the diode and power for the switching transistors is provided by the + 8 volt source through resistor R241.

When segment "1" is selected, transistor TR207 is turned on and transistor TR208 is turned off. PIN diode CD208 is forward biased causing it to turn on. This effectively places a short across capacitor C244 and ac grounds C243 in the Tx VCO.

When segment "2" is selected, transistor TR208 is turned on and TR207 is turned off. Diode CD208 is reverse biased causing it to turn off. L206 presents a high impedance to rf frequencies and the anode of CD208 is near dc ground and not at ac ground.

VCO CHARACTERISTICS

The synthesizer has two VCOs, the frequency of which is directly related to a control voltage generated by the synthesizer circuitry and must remain within specified limits for the synthesizer to function properly. The RX VCO typically will increase in frequency about 9.5 MHz when the control voltage moves from its lower limit to its upper limit. The TX VCO moves about 9.5 MHz on each split respectively for the same situation.

Table 1 - Frequency Segment Selection

OUTLINE DIAGRAM

FEEDBACK BUFFERS

The RX injection and TX injection voltage output from the RX VCO and Tx VCO are supplied to the buffer and to the feedback buffer. Buffer IC208 provides typical output of +2dBm to Tx/RX INJECTION P201. Feedback buffer is provided by IC204 and the output applied to dual-modulus prescaler IC202.

DUAL-MODULUS PRESCALER

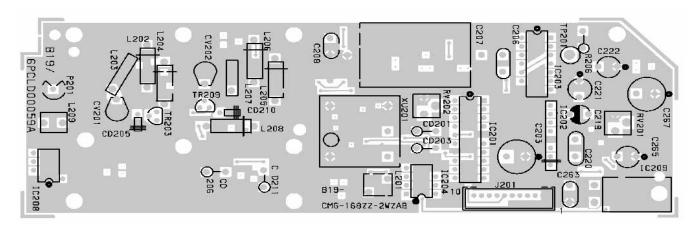
The dual-modulus prescaler (IC204) completes the PLL feedback path from the synthesizer to loop filter, to the VCOs and feedback buffer, and then back to the synthesizer through the prescaler. The prescaler divides the VCO frequency by 128 or 129 under control of N counter in the synthesizer IC.

The output of the prescaler is applied to the synthesizer where it is divided down to 6.25 kHz by an internal N and A counter and compared in frequency and phase with the divided frequency from the reference oscillator. The result of this comparison Is the error voltage used to maintain frequency lock. The divide by N and A counters are controlled by data received from the microcontroller. Depending on the operating frequency, the dc voltage at TP201 should be within the range of 3.5 and 7.5 Vdc when the PLL is locked.

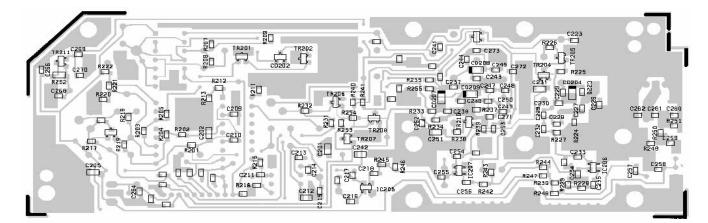
MODULATION LEVEL CONTROL

The modulation level control circuit automatically sets the TX Audio level applied to the transmit VCO modulator CD207, depending on the setting of VCO MOD ADJ control RV202. The modulation level control circuit consists of R231, R232, and TR206.

Modulation level is controlled by turning transistor switch TR206 on or off (under control of IC706), which adds (or removes) attenuator R232 to the circuit. Resistors R231 and R232 form an adjustable voltage divider used to change the modulation level as required.



SOLDER SIDE



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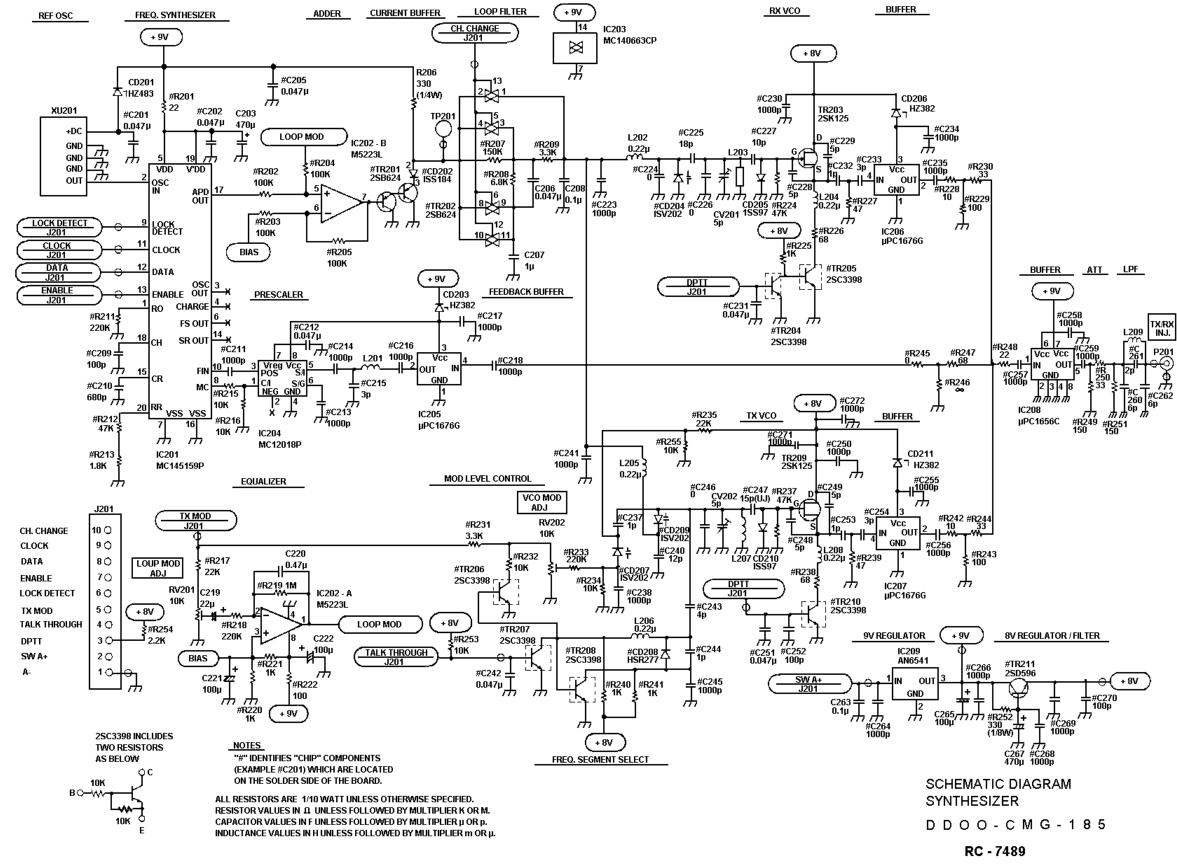
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COMPONENT SIDE

SYNTHESIZER BOARD

LBI-38350

SCHEMATIC DIAGRAM



SYNTHESIZER

PARTS LIST

SYNTHESIZER BOARD B19/CMG-185 ISSUE 1 SYMBOL PART NO. DESCRIPTION ---- CAPACITORS -B19/5CAAD01131 Ceramic: 0.047 uF <u>+</u>108, 25 VDCW. C201 and C202 C203 Electrolytic: 470 μ F ±20%, 16 VDCW. B19/5CEAA01829 C205 B19/5CAAD01131 Ceramic: 0.047 uF ±10%, 25 VDCW. C206 B19/5CRAA00628 Metallised plastic: 0.047 uP $\pm 5\%$, 50 VDCM. C207 819/5CRAH00066 Metallized plastic: 1 uF ±10%, 200 VDCW. C708 B19/5CRAA00617 Hetallized plastic: 0.1 uF ± 54 , 50 VDCM. Ceramic: 100 pF \pm 5%, 50 VDCW, tamp coef 0 \pm 30 PPM. C209 BL9/SCAADGO839 Ceramic: 680 p# +5%, 50 VDCM, temp coef +350 -1000 PPM. C210 819/SCAAD01063 819/5CAAD01154 Ceramic: 1000 pF ±10, 50 VDCW, temp coef +350 -1000 PPN. C211 C212 B19/5CAAD01131 Ceramic: 0.047 uF $\pm 10\%,~25$ VDCM. Ceramic: 1000 pF +10%, 50 VDCW, temp coef +350 -1000 PFM. C213 and C214 B19/5CARD01154 Ceramic: 3 pF 10.25 pF, 50 VDCN, temp coef 0 +30 PPN. 0215 B19/5CAAD00853 Geramic: 1000 pF ±10%, 50 VDGN, temp coel +350 -1000 PFM. 0216 thru 0218 819/5CAAD01154 C219 B19/5CSAC01129 $\texttt{Tantalum:} \quad 2\cdot 2 \text{ uf } \pm 10\%, \text{ } 25 \text{ VDCM}.$ Netallized plastic: 0.47 uF ±5%, 50 VDCW. C2 20 B19/5CRBA00838 C221 and C222 B19/5CERA01827 Electrolytic: 100 uF ±20%, 16 VDCN. C223 B19/5CRAD01154 Ceramic: 1000 pF ±10%, 50 VDCW, temp coe(+350 -1000 PPM. C225 819/5CAAD00963 Ceramic: 18 pF 15%, 50 VDCN, temp coef 0 130 PPM C227 819/5CAAD00953 Ceramic: 10 pP ± 0.5 pP, 50 VDCN, temp coef 0 ± 30 PPN. C228 and C229 819/5CAAD00956 Ceramic: 5 pF ± 0.25 pF, 50 VDCM, temp coef 0 ± 30 PPM. 819/5CAAD01154 Ceramic: 1000 pF $\pm 10\%$, 50 VDCN, temp coef +350 -1000 PPN. C230 C231 BI9/SCAAD01131 Ceramic: 0.047 uF +10%, 25 VDCN. Coramic: 1 pF ±0.25 pF, 50 VDCW, temp coef 0 ±30 PFM. C232 B19/5CAAD00852 Ceramic: 3 pF ± 0.25 pF, 50 VDCW, temp coef 0 ± 30 PFM. B19/SCAAD00653 C2 3 3 0234 and 0235 B19/5CAAD02154 Ceramic: 1000 pF +10%, 50 VDCN, temp coef +350 -1000 PPK. C237 819/5CAAD00857 Corponia: 1 pF ± 0.25 pF, 50 VDCW, temp coef 0 ± 30 PPM. Ceramic: 1000 pF ±10%, 50 VDCW, temp coef +350 -1000 PPM. B19/5CAAD01154 C238 Ceramíc: 12 pF ±5%, 50 VDCW, temp coef 0 +30 PPM 819/5CAAD00968 0240 Ceramic: 1000 pF 10%, 50 VDCW, temp coef +350 -2000 PPM. 0241 B19/5CARD01154 C242 819/5CAAD01131 Cecamic: 0.047 uP $\pm 10\%,~25$ VDCN. C243 B19/5CAAD00961 Contamic: 4 pF ± 0.25 pF, 50 VDCM, temp coef 0 ± 30 PPN. Ceramic: 1 pF ±0.25 pF, 50 VDCN, Lemp coef 0 ±30 PFA. C244 B19/5CAAD00B52 Coramic: 1000 pF $\pm 10\%$, 50 VDCW, temp coef +350 -1000 PPM. C245 B19/SCARD01154

PARTS LIST

SYMBOL	PART NO.	DESCRIPTION
C247	B19/5CAAD01423	Ceramic: 15 pF ±5%, 50 VDCW, temp coef -750 ±120
C248 and C249	B19/5CAAD00956	PPN. Ceramic: S pF ±0.25 pF, 50 VDCW, temp coef 0 ±30 PPM.
C249 C250	B19/5CAAD01154	Ceramic: 1000 pF ±10%, 50 VDCW, temp coef +350 -1000 PPN.
C251	B19/5CAAD01131	Ceramic: 0.047 uF <u>+</u> 10%, 25 VDCW.
C252	B19/5CAAD00839	Ceramic: 100 pF ±5%, 50 VDCW, temp coef 0 ±30
C253	B19/5CAAD00852	PPM. Ceramic: 1 pF \pm 0.25 pF, 50 VDCW, temp coef 0 \pm 30
G254	B19/5CAAD00853	PPM. Ceramic: 3 pP ±0.25 pP, 50 VDCW, temp coef 0 ±30
C255	B19/5CAAD01154	РРМ. Ceramic: 1000 pF ±10%, SO VDCW, temp coef +350
thru C259		-1000 PPN.
C260	B19/5CAAD00962	Ceramic: 6 pF ±0.5 pF, 50 VDCW, temp coef 0 ±30 FPM.
C261	B19/5CAAD00949	Ceramic: 2 pF ± 0.25 pF, 50 VDCW, temp coef 0 ± 30 PPM.
C262	B19/5CAAD00962	Ceramis: б pF ±0.5 pF, 50 VDCN, temp coef 0 ±30 PPM.
C263	B19/5CRAA00617	Metallized plastic: 0.1 uP ±5%, 50 VDCW.
C264	B19/5CAAD01154	Ceramic: 1000 pF <u>+</u> 10%, 50 VDCN, temp coef +350 -1000 PPM.
C265	B19/5CEAA01827	Electrolytic: 100 uF ±20, 16 VDCM.
C266	B19/5CAAD01154	Geramic: 1000 pF $\pm 10\%$ 50 VDCW, temp coef +350 -1000 PPM.
C267	B19/5CEAA01829	Electrolytic: 470 uF ±20%, 16 VDCW.
C268 and C269	B19/5CAAD01154	Ceramic: 1000 pF ±10%, 50 VDCN, temp coef +350 -1000 FPM .
C270	B19/5CAAD00839	Ceramic: 100 pF ±5%, 50 VDCN, temp coef 0 ±30 PPM.
C271 thru C273	B19/5CAAD01154	Ceramic: 1000 pF ±10%, 50 VDCW, temp coef +350 -1000 PPH.
		DIODES
CD201	B19/5TXAE00587	Zener: 4V, sim to HITACHI HZ4B3.
CD202	B19/5TXAD00290	Silicon, fast recovery (2 dicdes in Cathode common), sim to TOSHIBA 188184.
CD203	B19/5TXAE00566	Zener: 3V, sim to HITACHI HZ3B2.
CD204	B19/5TXAE00690	Silicon, Variable Capacitance Diode; sim to HITACHI ISV202.
CD205	B19/5TXAA00326	Silicon, Schottky Barrier; sim to NEC ISS97.
CD205	B19/5TXAE00566	Zener: 3V, sim to HITACHI HZ3B2.
CD207	B19/5TXAE00690	Silicon, Variable Capacitance Diode; sim to HITACHI ISV202.
CD208	B19/5TXAE00686	Silicon, Epitaxial planar; sim to HITACHI MSR277.
CID209	B19/5TXAE00690	Silicon, Variable Capacitance Diode; sim to RITACHI ISV202.
CD210	B19/5TXAA00326	Silicon, Schottky Barrier; sim to NEC 18897.
CD211	B19/5TXAE00566	Zener: 3V, sim to HITACHI HZ3B2.
CV201	B19/5CVBB00093	Variable: 5P max.
CV 20 2	B19/5CVAB00093	Variable: 5P max.
10201	B19/5DAAJ00328	
10202	B19/5DDAB00164	MC145159P. Linear Dual OP Amp; sim to NITSUBISHI M5223L.
10202	B19/5DAAJ00359	Digital Bilateral Switch; sim to MOTOROLA MC140668CP.
10204	B19/5DAAJ00574	MC140668CP. Prescaler, sim to MOTOROLA MC12018P.
10204	B19/5DAAA00284	RF Wide band amplifier; sim to NEC uPC1676G.
thru 10207		
10208	B19/5DAAA00183	RF Wide band amplifier; sim to uPC1656C.

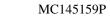
SYMBOL	PART NO.	DESCRIPTION
IC204	B19/50ARK00071	Linear, Positive voltaue regulator; Sim to MATSUSHITA AN6541.
		MATSUSHITA ANGS41.
		CONNECTORS
J.501	B19/5JWAV00121	Connector: 10 pins.
L201	B19/6LAFD01241	COILS
1202	B19/5LCACOOB82	Coil, #F: D.72 uH.
2202	B19/6LALD00087	Coil. RP.
L204	E19/SLCACOOBE2	Coll, RF: 0.22 uH.
thru 6206		
6207	\$19/SLALDCOCBO	Coll, SF.
r506	819/51CAC00882	Coil, SF: 0.22 uH.
L209	B19/5LALD00038	Coll. RF.
		PLUGS
6507	619/633FD00030	Connector, RF.
		RESISTORS
R201	619/580Ac02465	Metal Film: 22 ohma <u>⊀</u> 5%, 100 Vnic¥, 1/14¥.
8202 thru 8205	819/5RDAC02449	Metal Film: 100К ohmus <u>1</u> 5%, 100 VDCN, 1/10М.
R206	819/5RDAA01480	Carbon film: 330 ohmes ±54, 300 VDCW, 1/40.
R207	819/5RDAC02455	Metal Film: 150% obmas <u>≜</u> 54, 100 VDCW, 1/10W.
H200	619/5RDAC02458	Metal Film: 6.8K ohmus <u>₹</u> 5%, 100 vocw, 1/10m,
R209	B19/5RDAC02462	Metal Film: 3.3K ohmos <u>+</u> 5%, 100 VDCW, 1/10W.
R211	819/5RDAC02453	Metal Film: 220K ohmas ±5%, 100 VDCW, 1/16W.
R212	819/5RDAC02439	Metal Film: 47K obmus ±54, 100 VDCW, 1/1004.
R213	819/5RDAC02475	Metal Film: 1.8X ohmus ±54, 100 VDCW, 1/10N.
R215 and	B19/SRDAC02445	Metal Film: 10K ohmus ±5%, 100 VDCW, 1/10W.
R216		
R217	819/5R0AC02454	Metal Film: 22K ohmas <u>1</u> 5%, 100 VOCM, 1/10M.
#219	819/5RDAC02453	Metal Film: 220K ohmos <u>4</u> 5%, 100 VDCN, 1/100.
R219	919/3RDAC02461	Metal Film: 1.K ohmas 15%, 100 VDCW, 1/10W.
R220 and R221	B19/5RDAC02446	Metal Film: IK ohmas ±5%, 100 VDCM, 1/1004.
R222	819/5RDAC02447	Metal Film: 200 ohmus ±54, 100 VOCH, 1/100.
R224	819/5RDAC02439	Metal Film: 47K obmas 15%, 100 VOC%, 1/10W.
R225	819/5RDAC02446	Metal Film: ೩K ohmus <u>€</u> 5%, 100 VDCNF, 1/1014.
R226	B19/5RDAC02467	Metal Film: 68 ohma <u>±</u> 5%, 100 VDCN, 1/10M.
H227	B19/5RDAC02460	Metal Film: 47 ohmas ±5%, 100 VDCN, 1/100.
R228	819/SRDAC02450	Metal Film: 10 ohma ±5%, 200 VDCN, 1/10W.
8229	B19/5RDAC02447	Metal Film: 100 ohma <u>*</u> 5%, 100 ¥00%, 1/10₩,
R230	819/5RDAC02466	Metal Film: 33 ohma ±5%, 200 VDCN, 1/10H.
R231	819/5RDAC02462	Metal Film: 3.38 obms <u>4</u> 5%, 100 VDCN, 1/10₩.
R232	B19/5ROAC02445	Metal Film: 10K ohma ±5%, 100 VDCM, 1/10W.
R233	B19/5HDACU2453	Metal Film: 220X obmes ∱58, 100 VDCN, 1/10W. Metal Film: 10x obmes +58, 100 VDCN, 1/10W.
R234	819/58DAC02445	
R235 R237	819/SRDAC02454 819/SRDAC02439	Metal Film: 22K obmu 25%, 100 VDCN, 1/1094. Metal Film: 47K obmut ±5%, 100 VDCN, 1/1094.
R230	819/SKDAC02439 819/SHDAC02467	Metal Film: 47x oxmus ±5%, 500 VDCM, 1/10W. Metal Film: 56 oxmus ±5%, 500 VDCM, 1/10W.
R239	B19/5RDX/02460	Metal Film: 47 phms ±5%, 100 VDCW, 1/10W.
R240	B19/5RDAC07446	Metal Film: 1K ohms ±5%, 100 VDCW, 1/10W.
and R241		
R242	B19/5RDAC02450	Metal film: 10 ohms ±5%, 100 VDCW, 1/10w.
R243	B19/5RDAC02447	Metal Film: 100 ohms ±5%, 100 VDCW, 1/10W.
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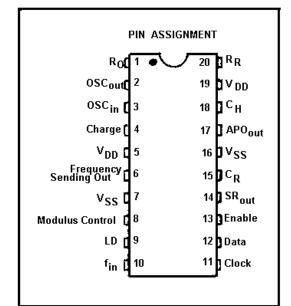
*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

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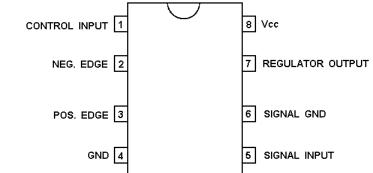
SYMBOL	PART NO.	DESCRIPTION
R244	B19/5RDAC02466	Metal film: 33 obms ±5%, 100 VDCW, 1/10W.
R247	B19/5RDAC02467	Hetal film: 68 ohms <u>+</u> 5%, 100 VDCW, 1/10W.
R248	B19/5RDAC02465	Metal film: 22 ohms ±5%, 100 VDCW, 1/10W.
R249	B19/5RDAC02468	Hetal film: 150 ohms ±5%, 100 VDCW, 1/10W.
R250	B19/5RDAC02466	
R251	B19/5RDAC02468	
R252	819/5RDAC02140	Metal film: 330 ohms ±5%, 100 VDCW, 1/8W,
R253	B19/5RDAA02445	Metal film: 10K ohms ±5%, 100 VDCW, 1/10W.
R254	819/5RDAA02451	Netal film: 2.2K ohms ±5%, 100 VDCW, 1/10W.
R255	B19/5RDAA02445	Hetal film: 10K ohms ±5%, 100 VDCW, 1/10W.
RV201 and RV202	B19/5RVAB00399	Variable: 10K ohms, 0.1W.
	910/57793700055	TRANSISTORS
TR201 and TR202	B19/5TBAB00055	Silicon, PNP: sim to NEC2SB624 (BV3).
TR203 TR204	819/5TKAH00006 819/5TCA200011	N-channel field effect (Junction Single Gate); sim to SONY 25K125. Silicon, NPN: sim to SANYO 28C3398
thru TR208		
TR209	B19/5TKAH00006	N-channel field effect (Junction Single Gate); sim to SONY 25%125.
TR210	B19/5TCA200011	Silicon, NPN: sim to SANYO 2SC3398.
TR211	819/5TDAB00054	Silicon, NPM: sim to NEC 25D596 (DV3).
KU2 01	B19/6XNLD00010	Reference Oscillator Unit.

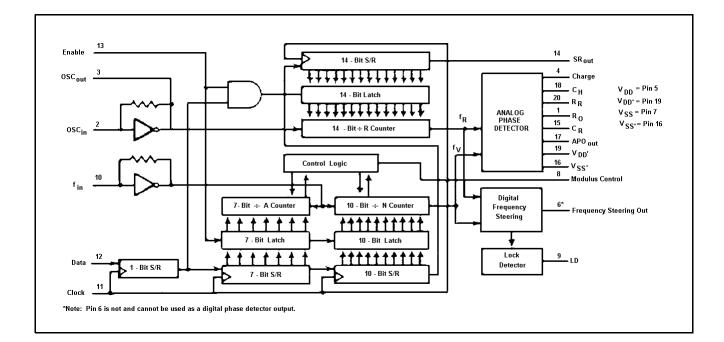
IC DATA



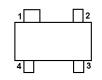








WIDE BAND AMPLIFIER (IC205 THROUGH IC207)



1. GND 2. OUTPUT 3. Vcc 4. INPUT

PHASE LOCK LOOP (PLL) (IC201)

DUAL-MODULUS PRESCALER (IC204)

MC12018

RC - 7042

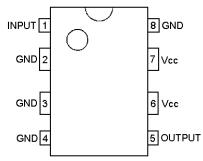
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IC DATA

WIDE BAND AMPLIFIER (IC208)

NEC uPC1656C

PIN ASSIGNMENT

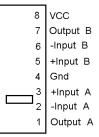


DUAL OPERATIONAL AMPLIFIER

(IC202)

MITSUBISHI M5223L

PIN ASSIGNMENT



LBI-38350

WIDE-BAND AMPLIFIER (IC208)